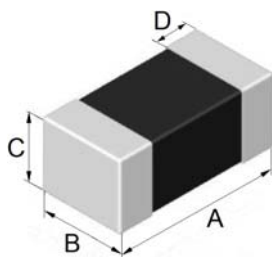


1. Dimension



Series	A(mm)	B(mm)	C(mm)	D(mm)
1210	3.20+0.60/-0.20	2.50+0.40/-0.20	2.60 max.	0.50±0.25

2. Part Numbering

TVS
1210
SN
750
-
040
K

A B C D E F

A: Series

B: Dimension

C: Super High Network

D: Breakdown voltage 750=75V

E: surge voltage 040=4KV

F: Inner Code

3. Specification

TAI-TECH Part Number	Maximum allowable continuous AC voltage at 50-60Hz V_{RMS} (V)	Maximum allowable continuous DC voltage V_{DC} (V)	Breakdown voltage V_B (V)	Maximum allowable clamping voltage V_C (V)	Maximum peak current (10/700 μ s) I_{PEAK} (A)	Maximum surge voltage (10/700 μ s) I_{Surge} (KV)	Maximum peak current (8/20 μ s) (15 time) I_{PEAK} (A)
TVS1210SN750-040K	48	60	75(\pm 10)	100	100	4	500
TVS1210SN750-060K	48	60	75(\pm 10)	100	150	6	500

Notes :

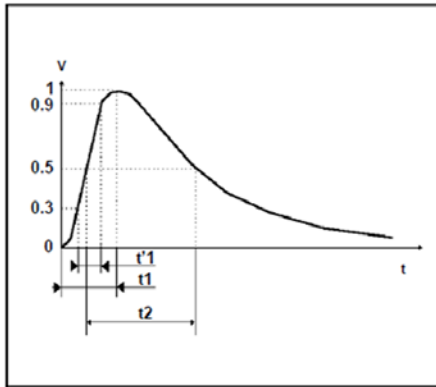
1. The breakdown voltage was measured at 1mA current.
2. The clamping voltage was measured at 8/20 μ s standard current, 1210(2.5A)
3. The surge current was tested at 10/700 μ s waveform, Ri=40ohm. Common-mode testing is to test all data lines while the GND

3-1. Reference Data			
ITEM	Symbol	Unit	Value
Typical capacitance value measured at 1KHz	C	pF	TVS1210SN750-040K : 1000 TVS1210SN750-060K : 1300
Response time	Trise	ns	< 1
Non-linear coefficient	α		> 30
Leakage current at $V_B \times 80\%$ (at initial state)	I_{VB}	μ A	< 10
Leakage current at $V_B \times 80\%$ (after surge test)	I_{VVA}	μ A	< 80
Operation ambient temperature	T_{OPT}	$^{\circ}$ C	-55~+125
Storage temperature range	T_{STG}	$^{\circ}$ C	-55~+150
3-2. Other Data			
Body	Nano special ceramic		
End termination	Ag/Ni/Sn		
Packaging	Reel		
Complies with standard	IEC61000-4-5 ITU-T K20, K21 UL1449,File No.E334409-VZCA2		
Complies with RoHs standard	Yes		
Lead content	< 1000 ppm		
Marking	None		

Notes :

1. The capacitance value only for customer reference, it's not formal specification.
2. The components shall be employed within 1 year, in the nitrogen condition.

4. Surge Wave Form



10/700µs waveform current

K21 Standard

SEVERITY LEVEL	t1 (=1.67t'1)	t2
1	10µS	700µS

Equivalent Circuit

L	Body Inductance
C	Device Capacitance
VR	Voltage Variable Resistor
R	Insulation Resistor
Diode	Voltage Clamped
PTC	for Low Leakage Current

